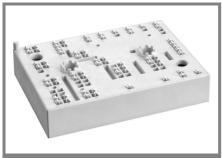
SKiiP 36NAB126V1



MiniSKiiP® 3

3-phase bridge rectifier + brake chopper + 3-phase bridge inverter **SKIIP 36NAB126V1**

Features

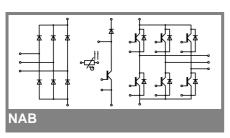
- Fast Trench IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

Typical Applications

- Inverter up to 36 kVA
- Typical motor power 18,5 kW

Remarks

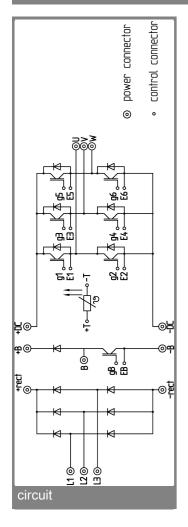
• V_{CEsat} , V_F = chip level value

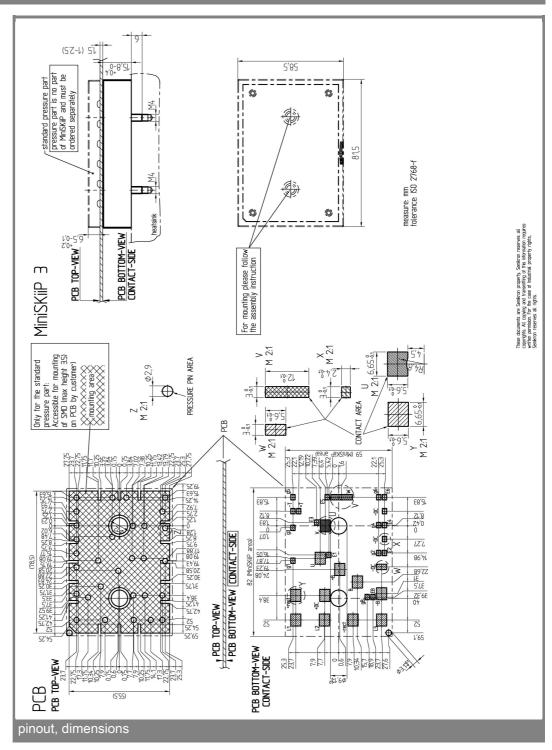


Absolute Maximum Ratings T _s = 25 °C, unless otherwise specifie							
Symbol	Conditions	Values	Units				
IGBT - Inverter, Chopper							
V_{CES}		1200	V				
I _C	T _s = 25 (70) °C	88 (66)	Α				
I _{CRM}	$t_p \le 1 \text{ ms}$	140	Α				
V_{GES}		± 20	V				
T _j		- 40 + 150	°C				
Diode - Inverter, Chopper							
I _F	T _s = 25 (70) °C	91 (68)	Α				
I _{FRM}	$t_p \le 1 \text{ ms}$	140	Α				
T _j		- 40 + 150	°C				
Diode - Rectifier							
V_{RRM}		1600	V				
I _F	$T_s = 70 ^{\circ}C$	61	Α				
I _{FSM}	$t_p = 10 \text{ ms, sin } 180 ^\circ, T_i = 25 ^\circ\text{C}$	700	Α				
i²t	$t_p = 10 \text{ ms, sin } 180 ^\circ, T_j = 25 ^\circ\text{C}$	2400	A²s				
T _j		- 40 + 150	°C				
I _{tRMS}	per power terminal (20 A / spring)	80	Α				
T _{stg}	$T_{op} \le T_{stg}$	- 40 + 125	°C				
V _{isol}	AC, 1 min.	2500	V				

Characte	ristics	Γ _s = 25 °C, unless otherwise specified								
Symbol	Conditions	min.	typ.	max.	Units					
IGBT - Inverter, Chopper										
$\begin{matrix} V_{\text{CEsat}} \\ V_{\text{GE(th)}} \\ V_{\text{CE(TO)}} \end{matrix}$	$I_{Cnom} = 70 \text{ A}, T_j = 25 (125) ^{\circ}\text{C}$ $V_{GE} = V_{CE}, I_C = 3 \text{ mA}$ $T_j = 25 (125) ^{\circ}\text{C}$	5	1,7 (2) 5,8 1 (0,9)	2,1 (2,4) 6,5 1,2 (1,1)	V V V					
$\begin{aligned} & r_{T} \\ & C_{ies} \\ & C_{oes} \\ & C_{res} \\ & R_{th(j-s)} \end{aligned}$	$\begin{split} &T_{j} = 25 \text{ (125) }^{\circ}\text{C} \\ &V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, \text{ f} = 1 \text{ MHz} \\ &V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, \text{ f} = 1 \text{ MHz} \\ &V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, \text{ f} = 1 \text{ MHz} \\ &\text{per IGBT} \end{split}$		10 (16) 4,8 1 0,6 0,5	13 (19)	mΩ nF nF nF K/W					
$\begin{array}{c} t_{d(on)} \\ t_r \\ t_{d(off)} \\ t_f \\ E_{on} \\ E_{off} \end{array}$	under following conditions $V_{CC} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}$ $I_{Cnom} = 70 \text{ A}, T_j = 125^{\circ}\text{C}$ $R_{Gon} = R_{Goff} = 9 \Omega$ inductive load		80 25 390 90 9		ns ns ns ns mJ					
	Verter, Chopper I _{Fnom} = 70 A, T _j = 25 (125) °C T _j = 25 (125) °C T _j = 25 (125) °C per diode		1,5 (1,5) 1 (0,8) 7,1 (10) 0,7		V V mΩ K/W					
I _{RRM} Q _{rr} E _{rr}	under following conditions $I_{Fnom} = 70 \text{ A}, V_R = 300 \text{ V}$ $V_{GE} = 0 \text{ V}, T_j = 125 ^{\circ}\text{C}$ $di_F/dt = 2000 \text{ A}/\mu\text{s}$		77 18 7,5		Α μC mJ					
Diode - R	Diode - Rectifier									
V _F V _(TO) r _T	$I_{Fnom} = 35 \text{ A}, T_j = 25 \text{ °C}$ $T_j = 150 \text{ °C}$ $T_j = 150 \text{ °C}$ per diode		1,1 0,8 11 0,9		V V mΩ K/W					
R _{th(j-s)}	<u>l'</u>		0,3		17/ 7/					
R _{ts}	ure Sensor 3 %, T _r = 25 (100) °C		1000(1670)		Ω					
Mechanic	Mechanical Data									
w M _s	Mounting torque	2	95	2,5	g Nm					

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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.